



FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.

990559

SERIAL NO.

09/320,271

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

WATANABE et al.

FILING DATE

May 27, 1999

GROUP

2825

(Use several sheets if necessary)

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EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
CL	AA	5,024,723	06/18/91	Goesele, et al.	156	628	
	AB	5,616,513	04/01/97	Shepard	438	402	
	AC	5,674,784	10/07/97	Jang, et al.	437	195	
	AD	5,723,895	03/03/98	Takahashi	257	499	
	AE	5,830,773	11/03/98	Brennan, et al.	437	67	
	AF	5,581,101	12/3/96	Ning et al.	257	347	
	AG	4,962,052	10/09/90	Asayama, et al.	437	31	
	AH	5,930,624	07/27/99	Murata, et al.	438	253	
	AI	5,153,680	10/06/92	Naito, et al.	438	687	
	AJ	3,747,203	07/24/73	Shannon	438	629	
	AK	5,166,768	11/24/92	Ito	438	637	
	AL	4,676,867	06/30/87	Elkins, et al.	156	643	
	AM	4,775,550	10/04/88	Chu, et al.	427	38	
	AN	4,885,262	12/05/89	Ting, et al.	437	231	
	AO	4,983,546	01/08/91	Hyun, et al.	437	231	
	AP	5,003,062	03/26/91	Yen	437	231	
	AQ	5,106,787	04/21/92	Yen	437	231	
	AR	5,352,630	10/04/94	Kim, et al.	437	195	
	AS	5,549,786	08/27/96	Jones, et al.	156	662.1	
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	AU	5,270,259	12/1993	Ito, et al.	437	235	
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	BB	5,702,568	12/30/97	Shin, et al.	156	644	
	BC	5,314,834	08/26/91	Mazure, et al.	438	595	
	BD	5,866,476	02/02/99	Choi, et al.	438	624	
	BE	5,084,412	01/28/92	Nakasaki	437	189	
	BF	5,479,054	12/26/95	Tottori	257	752	
	BG	5,753,975	05/19/98	Matsuno	257	751	
	BH	6,013,578	01/2000	Jun	438	687	
	BI	5,817,582	10/06/98	Maniar	438	782	
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	BM	5,855,962	01/05/99	Cote, et al.	427	376	
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CL	BO	02-235358	09/18/90	Japan	Abstract	
	BP	JP 6-291202	10/18/94	Japan	Abstract	
	BQ	JP 63 198359	8/17/88	Japan	Abstract	
	BR	10-303295	11/13/98	Japan	Abstract	
	BS	59-017243	01/28/84	Japan	Abstract	
	BT	58-031519	02/24/83	Japan	Abstract	
	BU	10-209147	08/07/98	Japan	Abstract	
	BV	08-241891	09/17/96	Japan	Abstract	
	BW	09-330982	12/22/97	Japan	Abstract	
	BX	62-060242	03/16/87	Japan	Abstract	
	BY	01-199456	08/10/89	Japan	Abstract	
CL	BZ	03-101130	04/25/91	Japan	Abstract	

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C	CA	05-074963	03/26/93	Japan	Abstract	
	CB	06-349950	12/22/94	Japan	Abstract	
	CC	02-026055	01/29/90	Japan	Abstract	
	CD	04-234149	08/21/92	Japan	Abstract	
	CE	07-099195	04/11/95	Japan	Abstract	
	CF	02-253643	10/12/90	Japan	Abstract	
	CG	02-007451	01/11/90	Japan	Abstract	
	CH	08-017770	01/19/96	Japan	Abstract	
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	CJ	05-198523	08/06/93	Japan	Abstract	
	CK	04-317358	11/09/92	Japan	Abstract	
	CL	08-064561	03/08/96	Japan	Abstract	
	CM	01-307247	12/12/89	Japan		No
	CN	JP 56-125844	10/2/81	Japan	Abstract	
	CO	02-101532	08/13/90	Japan	Yes	
	CP	02-235358	09/18/90	Japan	Yes	
	CQ	04-307934A	10/30/92	Japan		No
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C	CS	"Multilevel-Interconnection Technology for VLSI and ULSI," Silicon Processing for the VLSI Era - Volume II, (pp. 232-233).
	CT	"Lithography I: Optical Resist Material and Process Technology," (pp. 441).
	CU	1995 Proceedings 12th International VLSI Multilevel Interconnection Conference (VMIC Catalog No. 95ISMIC - 104), June 27-29, 1995.
	CV	Wang, et al., "A Study of Plasma Treatments on Siloxane SOB," IEEE VMIC Conference, June 7-8, 1994, pp. 101-107.
C	CW	Chiang, et al., "D fencts Study on Spin on Glass Planarization Techn logy," IEEE VMIC Conference, June 15-16, 1987, pp. 404-412.

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CY	Moriya, et al., "Modification Effects in Ion-Implanted SiO <sub>2</sub> Spin-on-Glass," Journal of Electrochem. Soc., Vol. 140, No. 5, May 1993, pp. 1442-1450.
CZ	Matsuura, et al., "An advance Interlayer Dielectric System with Partially Converted Organic SOG Using Plasma Treatment," IEEE VMIC Conference, June 8-9, 1993, pp. 113-115.
DA	Ishida, et al., "Mechanism for AlSiCu Alloy Corrosion," Japanese Journal of Applied Physics, Vol. 31 (1992), pp. 2045-2048.
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DD	Murase, et al., "Dielectric Constant of Silicon Dioxide Deposited by Atospheric-Pressure Chemical Vapor Deposition Using Tetraethylorthosilicate and Ozone," Japanese Journal of Applied Physics, Vol. 33, (1994), pp. 1385-1389.

EXAMINER <i>calbomile</i>	DATE CONSIDERED 5.9.04
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>	

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<u>CL</u>	AR	Wolf et al. "Silicon Processing for the VLSI Era: Volume I - Process Technology," "Lattice Press, 1986 p. 441
<u>CL</u>	AS	Office Action of Japanese Application No. 09-234456.
<u>CL</u>	AJ	OFFICE Action of JAPANESE Application No. 08-181593.
<u>CL</u>	AU	Office Action of Japanese Applicarion No. 09-204942.
<u>CL</u>	AV	Office Action of Japanese Application No. 08-345587.
<u>CL</u>	AW	Office Action Of Japanese Application No. 09-012788.
<u>CL</u>	AX	Office Action of Japanese Application No. 07-227294.
	AY	

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Date Considered

5. 09. 04

### Related Copending Applications

<u>Application No.</u>	<u>Filing Date</u>	<u>Attorney Docket No.</u>	<u>Status</u>
CL 08/921,250	8/29/97	970813	Pending
08/806,425	2/26/97	970150	5,892,269 (Issued)
09/228,148	1/11/99	970150A	Pending
09/160,044	09/25/98	981187	6,235,648 (Issued)
09/716,334	11/21/00	981187A	Pending
CL 08/923,901	09/04/97	970952	6,288,438 (Issued)

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